

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AJT150** is Designed for 960 – 1215 MHz, JTIDS Applications.

**FEATURES:**

- Internal Input/Output Matching Network
- $P_G = 7.5$  dB at 150 W/ 1215 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.57 °C/W

**PACKAGE STYLE .400 2L FLG (A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.135 / 3.43	.145 / 3.68
B	.100 / 2.54	.120 / 3.05
C	.050 / 1.27	
D	.376 / 9.55	.396 / 10.06
E	.110 / 2.79	.130 / 3.30
F	.395 / 10.03	.407 / 10.34
G	.193 / 4.90	
H	.490 / 12.45	.510 / 12.95
I	.100 / 2.54	
J	.690 / 17.53	.710 / 18.03
K	.890 / 22.61	.910 / 23.11
L	.003 / 0.08	.006 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

**ORDER CODE: ASI10548**

**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_{BE} = 50$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
$P_G$ $\eta_c$	$V_{CC} = 50$ V $P_{OUT} = 150$ W $f = 960 - 1215$ MHz	7.5 40			dB %

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.